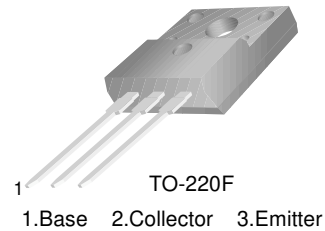


## FJPF6806D

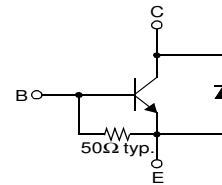
FJPF6806D

### High Voltage Color Display Horizontal Deflection Output (Damper Diode Built In)

- High Collector-Base Breakdown Voltage :  $BV_{CBO} = 1500V$
- High Switching Speed :  $t_f(\text{typ.}) = 0.1\mu s$
- For Color TV



Equivalent Circuit



### NPN Triple Diffused Planar Silicon Transistor

#### Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	750	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current (DC)	6	A
$I_{CP}^*$	Collector Current (Pulse)	12	A
$P_C$	Collector Dissipation	40	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{STG}$	Storage Temperature	-55 ~ 150	$^\circ C$

\* Pulse Test: Pulse Width=5ms, Duty Cycle  $\leq 10\%$

#### Electrical Characteristics $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$I_{CES}$	Collector Cut-off Current	$V_{CB}=1400V, R_{BE}=0$			1	mA
$I_{CBO}$	Collector Cut-off Current	$V_{CB}=800V, I_E=0$			10	$\mu A$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB}=4V, I_C=0$	40		200	mA
$BV_{EBO}$	Base-Emitter Breakdown Voltage	$I_E=300mA, I_C=0$	6			V
$h_{FE1}$ $h_{FE2}$	DC Current Gain	$V_{CE}=5V, I_C=1A$ $V_{CE}=5V, I_C=4A$	8 4		7	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=4A, I_B=1A$			5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=4A, I_B=1A$			1.5	V
$V_F$	Damper Diode Turn On Voltage	$I_F = 4.5A$			2	V
$t_{STG}^*$	Storage Time	$V_{CC}=200V, I_C=4A, R_L=50\Omega$			3	$\mu s$
$t_f^*$	Fall Time	$I_{B1}=1.0A, I_{B2}= - 2.0A$			0.2	$\mu s$

\* Pulse Test:  $PW=20\mu s$ , duty Cycle=1% Pulsed

#### Thermal Characteristics $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case		3.1	$^\circ C/W$

# Typical Characteristics

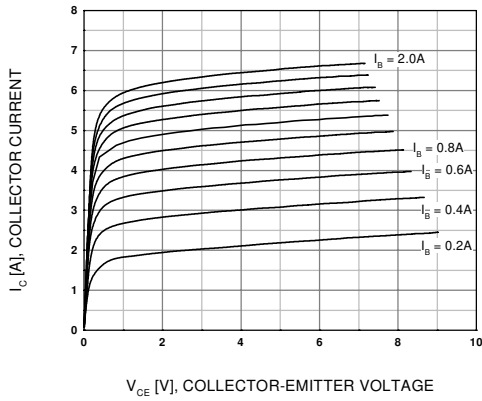


Figure 1. Static Characteristic

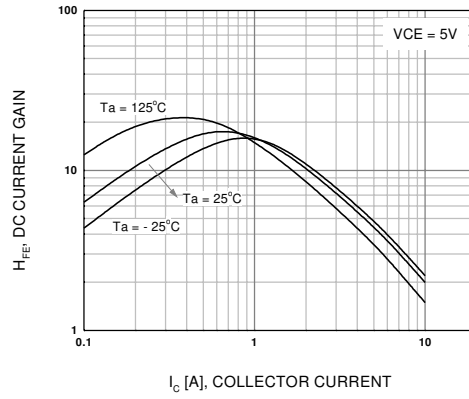


Figure 2. DC current Gain

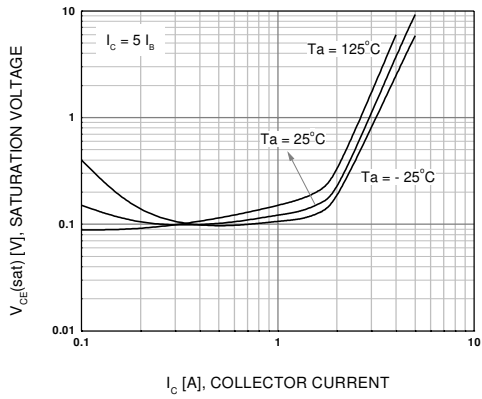


Figure 3. Collector-Emitter Saturation Voltage

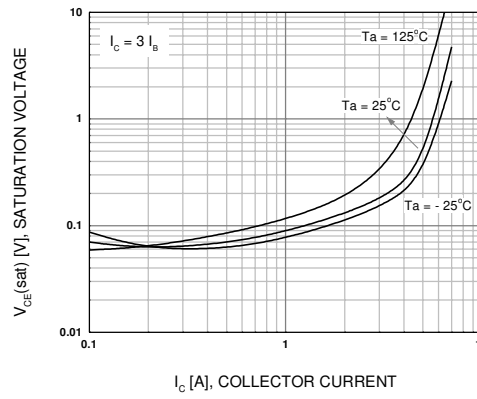


Figure 4. Collector-Emitter Saturation Voltage

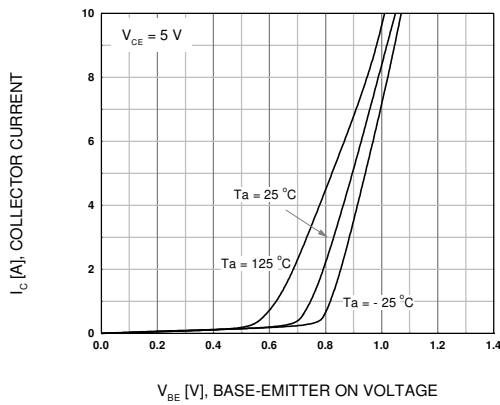


Figure 5. Base-Emitter On Voltage

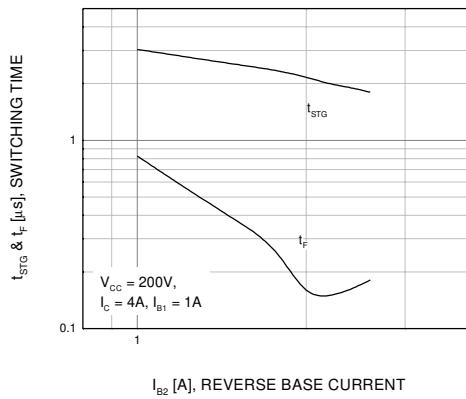


Figure 6. Resistive Load Switching Time

Typical Characteristics (Continued)

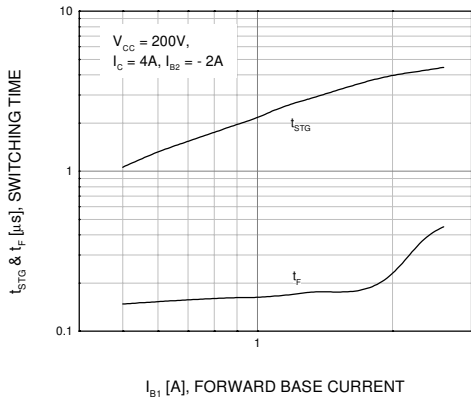


Figure 7. Resistive Load Switching Time

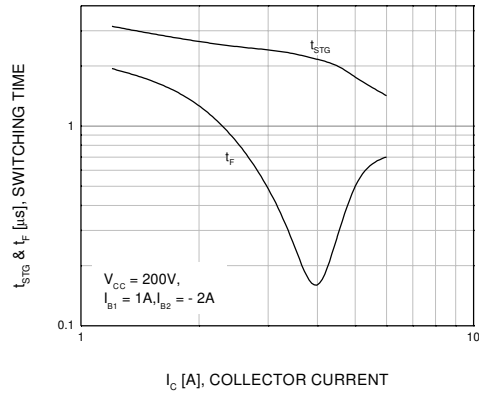


Figure 8. Resistive Load Switching Time

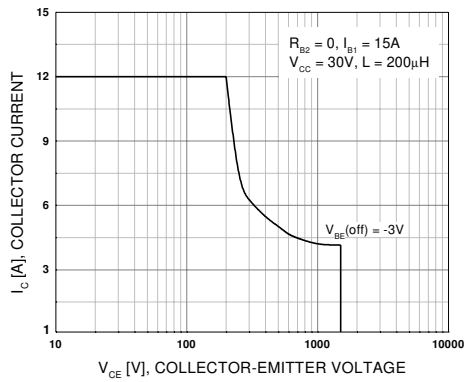


Figure 9. Reverse Bias Safe Operating Area

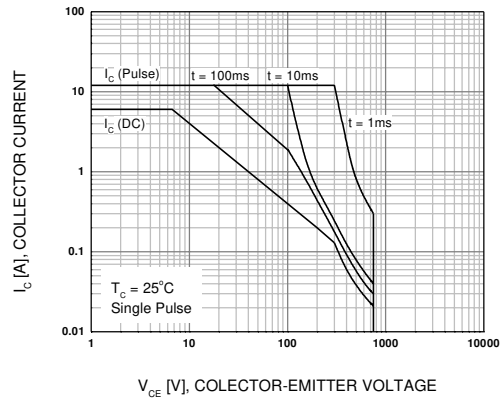


Figure 10. Forward Bias Safe Operating Area

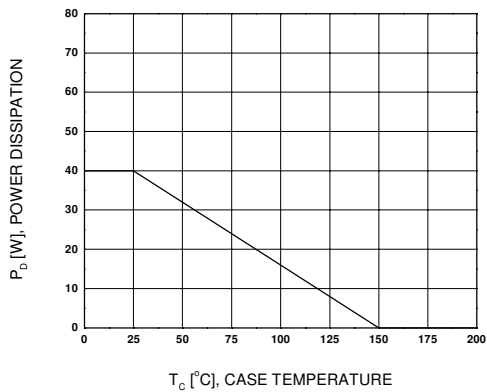
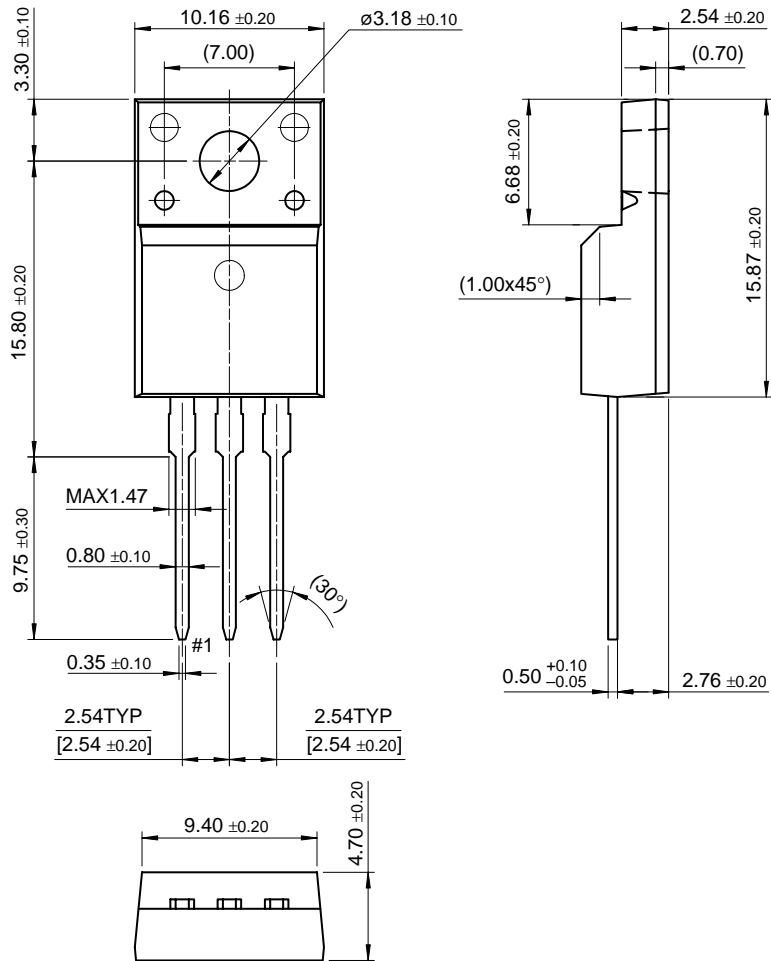


Figure 11. Power Derating

# Package Dimensions

FJPF6806D

## TO-220F



Dimensions in Millimeters

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CROSSVOLT <sup>™</sup>	GTO <sup>™</sup>	POP <sup>™</sup>	SuperSOT <sup>™</sup> -3	
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EcoSPARK <sup>™</sup>	I <sup>2</sup> C <sup>™</sup>	PowerTrench <sup>®</sup>	SuperSOT <sup>™</sup> -8	
E <sup>2</sup> CMOS <sup>™</sup>	ISOPLANAR <sup>™</sup>	QFET <sup>™</sup>	SyncFET <sup>™</sup>	
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FACT Quiet series <sup>™</sup>	MicroPak <sup>™</sup>	Quiet Series <sup>™</sup>	UHC <sup>™</sup>	
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